



PSMN008-75B,118 Information



For Reference Only

Part Number PSMN008-75B,118 **Manufacturer** Nexperia USA Inc.

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 75V 75A D2PAK

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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PSMN008-75B,118 Specifications

Manufacturer Part Number PSMN008-75B,118 Manufacturer Nexperia USA Inc. Category Discrete Semiconductor Products Fackage TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 75V Current - Continuous Drain (Id) @ 25°C 75A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ ImA Gate Charge (Qg) (Max) @ Vgs 122.8nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5260pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 230W (Tc) Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) T5V Current - Continuous Drain (Id) @ 25°C T5A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ ImA Gate Charge (Qg) (Max) @ Vgs 122.8nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5260pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Manufacturer Part Number	PSMN008-75B,118
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Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Toain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C T5A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) #20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Category	Discrete Semiconductor Products
SeriesTrenchMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)75VCurrent - Continuous Drain (Id) @ 25°C75A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ ImAGate Charge (Qg) (Max) @ Vgs122.8nC @ 10VInput Capacitance (Ciss) (Max) @ Vds5260pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)230W (Tc)Rds On (Max) @ Id, Vgs8.5 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) 75V Current - Continuous Drain (Id) @ 25°C 75A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 122.8nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5260pF @ 25V Vgs (Max) #20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case N-Channel NOSFET (Metal Oxide) 75V 75V 75V 75V 75V 75A (Tc) 10V 10V 10V 10V 122.8nC @ 10V 10V 122.8nC @ 10V 10V 10V 10V 10V 10V 10V 10V	Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 75A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 122.8nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5260pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 0perating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case MOSFET (Metal Oxide) 75V MOUNTED (Max) (Ma	Series	TrenchMOS?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 75A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 122.8nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5260pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 230W (Tc) Rds On (Max) @ Id, Vgs 0perating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case 75A (Tc) 75A	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 75A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 122.8nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5260pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 230W (Tc) Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case T0-263-3, D2Pak (2 Leads + Tab), TO-263AB	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 122.8nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 5260pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 230W (Tc) Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drain to Source Voltage (Vdss)	75V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **E20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 4V @ 1mA 4V @ 1mA 122.8nC @ 10V 5260pF @ 25V **E20V **E20V **E20V **E30W (Tc) **E30W (Tc) **E30W (Tc) **E50PF @ 25V **E30W (Tc) **E30W (T	Current - Continuous Drain (Id) @ 25°C	75A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 5260pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 5260pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs(th) (Max) @ Id	4V @ 1mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)230W (Tc)Rds On (Max) @ Id, Vgs8.5 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Gate Charge (Qg) (Max) @ Vgs	122.8nC @ 10V
FET Feature - Power Dissipation (Max) 230W (Tc) Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Input Capacitance (Ciss) (Max) @ Vds	5260pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 8.5 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Power Dissipation (Max)	230W (Tc)
Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case T0-263-3, D2Pak (2 Leads + Tab), T0-263AB	Rds On (Max) @ Id, Vgs	8.5 mOhm @ 25A, 10V
Supplier Device Package D2PAK Package / Case D2PAK TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Mounting Type	Surface Mount
	Supplier Device Package	D2PAK
Report errors?	Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
		Report errors?

PSMN008-75B,118 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

PSMN008-75B,118 Payment Methods



















PSMN008-75B,118 Shipping Methods













If you have any question about PSMN008-75B,118, please do not hesitate to contact us!

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